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# 2SB1025

Silicon PNP Epitaxial

# HITACHI

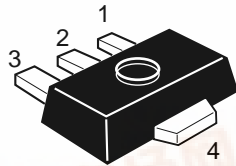
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## Application

- Low frequency power amplifier
- Complementary pair with 2SD1418

## Outline

UPAK



1. Base
2. Collector
3. Emitter
4. Collector (Flange)

## 2SB1025

### Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	-120	V
Collector to emitter voltage	$V_{CEO}$	-80	V
Emitter to base voltage	$V_{EBO}$	-5	V
Collector current	$I_C$	-1	A
Collector peak current	$i_{C(peak)}^{*1}$	-2	A
Collector power dissipation	$P_C^{*2}$	1	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW ≤ 10 ms, Duty cycle ≤ 20%

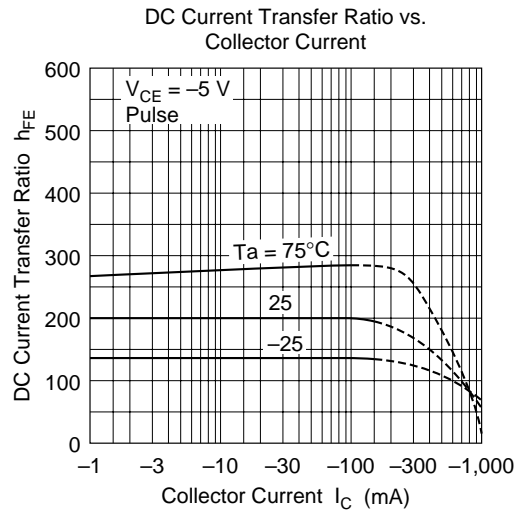
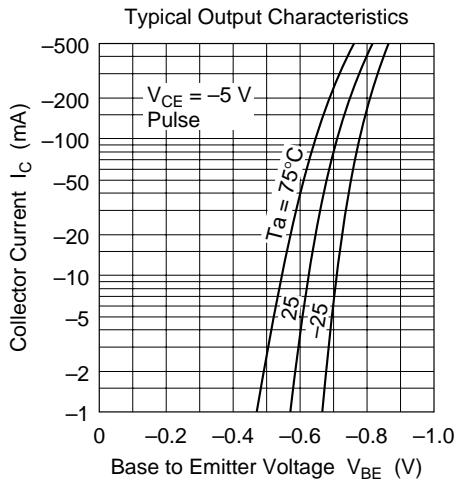
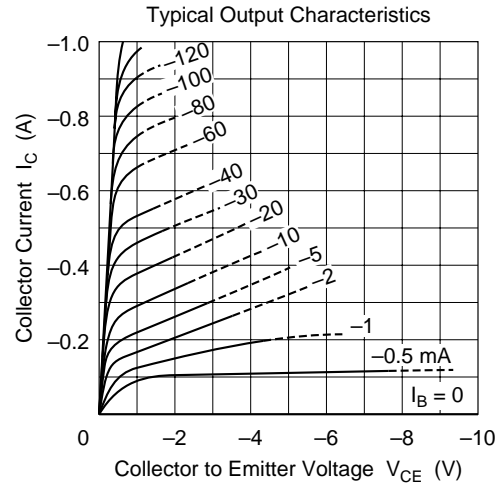
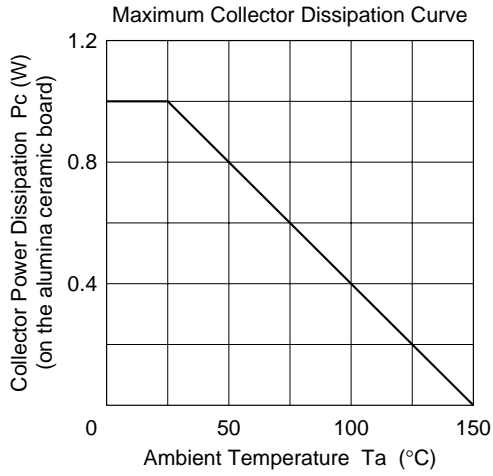
2. Value on the alumina ceramic board (12.5 × 20 × 0.7 mm)

### Electrical Characteristics (Ta = 25°C)

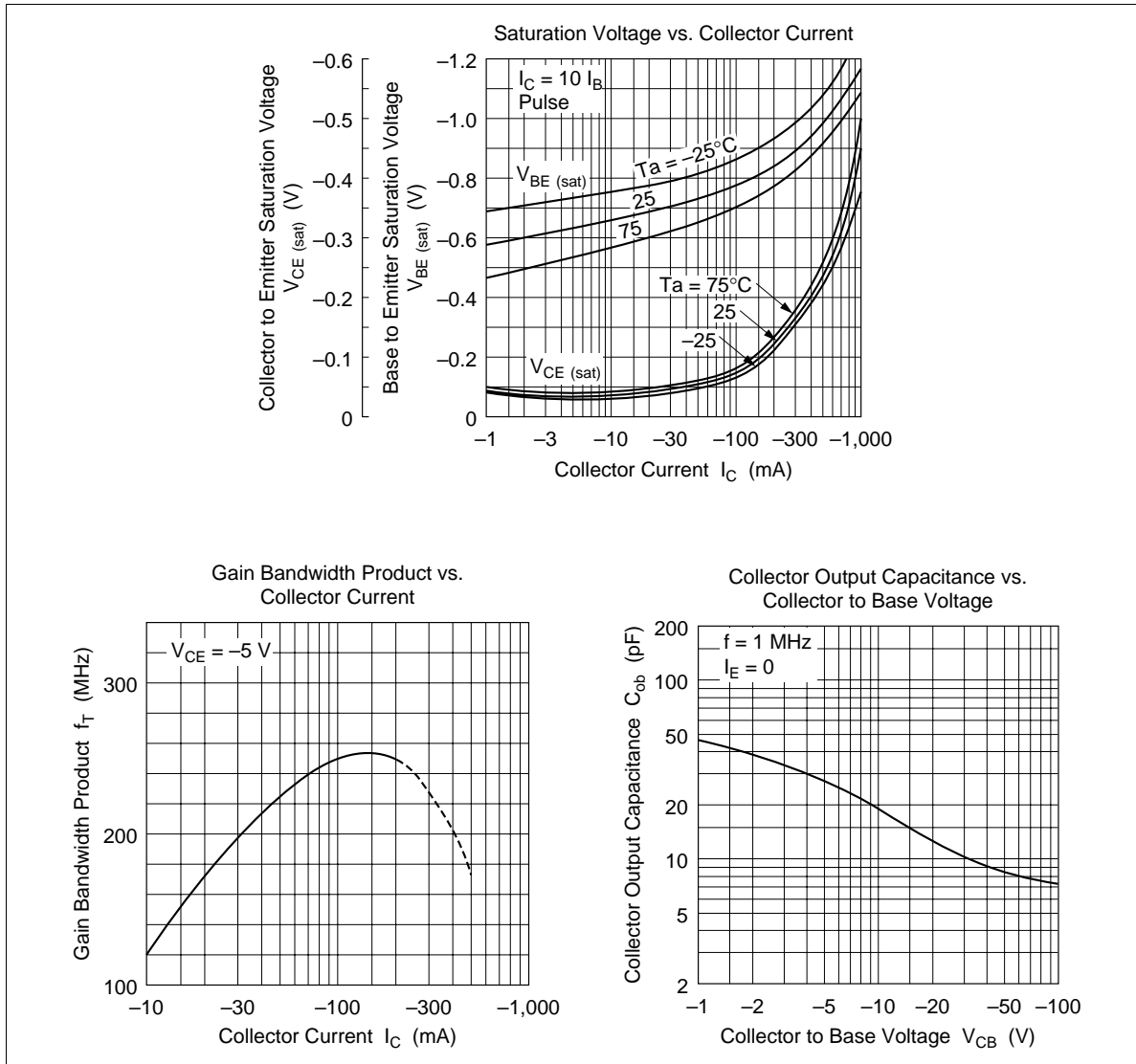
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-120	—	—	V	$I_C = -10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-80	—	—	V	$I_C = -1 mA, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	V	$I_E = -10 \mu A, I_C = 0$
Collector cutoff current	$I_{CBO}$	—	—	-10	$\mu A$	$V_{CB} = -100 V, I_E = 0$
DC current transfer ratio	$h_{FE1}^{*1}$	60	—	320		$V_{CE} = -5 V, I_C = -150 mA$
	$h_{FE2}$	30	—	—		$V_{CE} = -5 V,$ $I_C = -500 mA$ (Pulse test)
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-1	V	$I_C = -500 mA,$ $I_B = -50 mA$ (Pulse test)
Base to emitter voltage	$V_{BE}$	—	—	-0.9	V	$V_{CE} = -5 V, I_C = -150 mA$
Gain bandwidth product	$f_T$	—	140	—	MHz	$V_{CE} = -5 V, I_C = -150 mA$
Collector output capacitance	Cob	—	20	—	pF	$V_{CB} = -10 V, I_E = 0,$ $f = 1 MHz$

Note: 1. The 2SB1025 is grouped by  $h_{FE1}$  as follows.

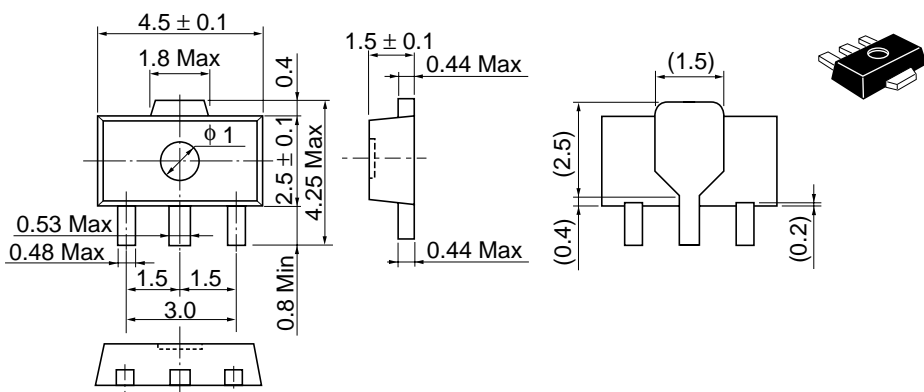
Mark	DH	DJ	DK
$h_{FE1}$	60 to 120	100 to 200	160 to 320



## 2SB1025



Unit: mm



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## Cautions

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